

# BC856BS 65 V, 100 mA PNP/PNP general-purpose transistor Rev. 01 — 11 August 2009 Produ

Product data sheet

## 1. Product profile

### 1.1 General description

PNP/PNP general-purpose transistor pair in a very small Surface-Mounted Device (SMD) plastic package.

#### Table 1. **Product overview**

Type number			NPN/NPN	NPN/PNP
	NXP	JEITA	complement	complement
BC856BS	SOT363	SC-88	BC846BS	BC846BPN

#### 1.2 Features

- Low collector capacitance
- Low collector-emitter saturation voltage
- Closely matched current gain
- Reduces number of components and board space
- No mutual interference between the transistors
- AEC-Q101 qualified

### **1.3 Applications**

General-purpose switching and amplification

#### 1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$V_{CEO}$	collector-emitter voltage	open base	-	-	-65	V
I <sub>C</sub>	collector current		-	-	-100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 V;$ $I_C = -2 mA$	200	290	450	



#### 65 V, 100 mA PNP/PNP general-purpose transistor

## 2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		1 2 3
			sym018

## 3. Ordering information

Table 4. Ordering information				
Type number	Package			
	Name	Description	Version	
BC856BS	SC-88	plastic surface-mounted package; 6 leads	SOT363	

## 4. Marking

Table 5. Marking codes	
Type number	Marking code <sup>[1]</sup>
BC856BS	*E6

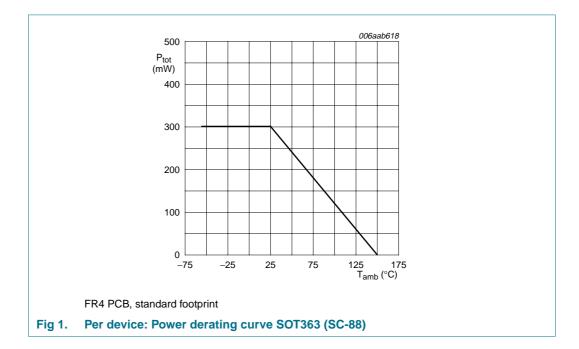
- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

#### 65 V, 100 mA PNP/PNP general-purpose transistor

## 5. Limiting values

Table 6. In accorda	Limiting values nce with the Absolute Maxim	um Rating System (I	IEC 60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
Per transi	stor				
V <sub>CBO</sub>	collector-base voltage	open emitter	-	-80	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-65	V
$V_{\text{EBO}}$	emitter-base voltage	open collector	-	-6	V
I <sub>C</sub>	collector current		-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \leq 1 \text{ ms}$	-	-200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \leq 1 ms$	-	-200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	200	mW
Per devic	e				
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	300	mW
Тj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

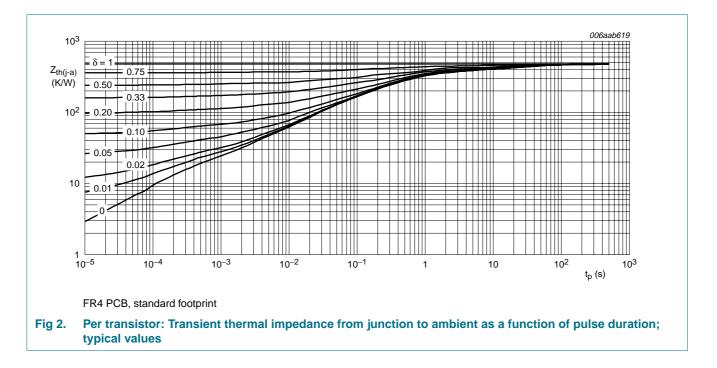


#### 65 V, 100 mA PNP/PNP general-purpose transistor

### 6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	625	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	230	K/W
Per devic	e					
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	416	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



BC856BS 1

### 65 V, 100 mA PNP/PNP general-purpose transistor

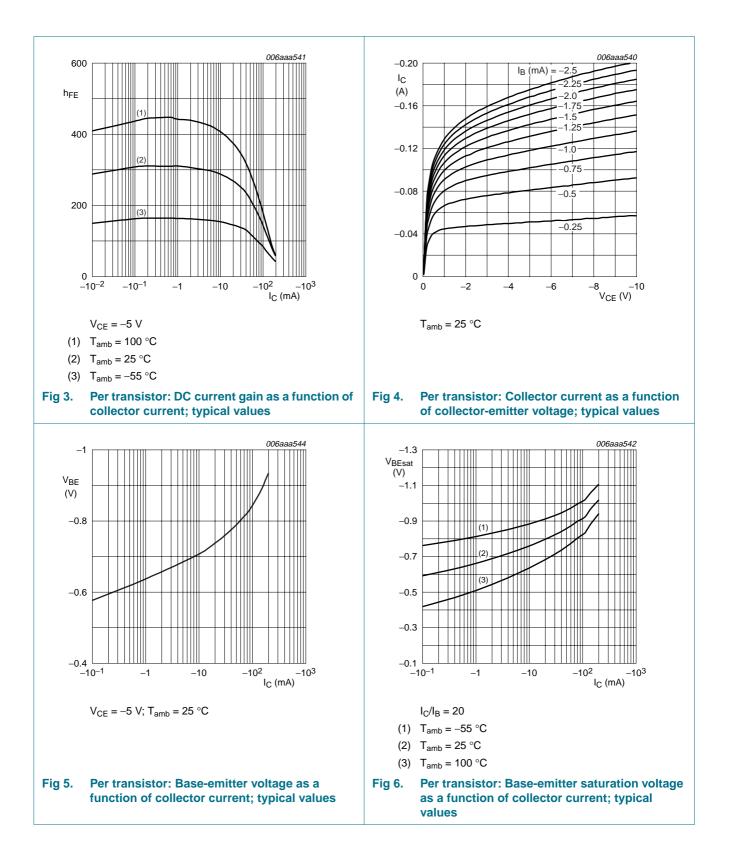
## 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor					
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -50$ V; $I_E = 0$ A	-	-	-15	nA
	current	$\label{eq:VCB} \begin{array}{l} V_{CB} = -30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \\ T_{j} = 150 \ ^{\circ}\text{C} \end{array}$	-	-	-5	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -6 V; I_C = 0 A$	-	-	-100	nA
h <sub>FE</sub> DC current gain		$V_{CE} = -5 V$				
		I <sub>C</sub> = -10 μA	-	270	-	
		$I_{\rm C} = -2  \rm{mA}$	200	290	450	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-55	-100	mV
	$I_{C} = -100 \text{ mA}; I_{B} = -5 \text{ mA}$	-	-200	-300	mV	
V <sub>BEsat</sub>	r <sub>BEsat</sub> base-emitter saturation voltage	$I_{C} = -10 \text{ mA};$ $I_{B} = -0.5 \text{ mA}$	-	-755	-850	mV
		$I_{\rm C} = -100 \text{ mA}; I_{\rm B} = -5 \text{ mA}$	-	-900	-	mV
V <sub>BE</sub>	base-emitter voltage	$V_{CE} = -5 V$				
		$I_{\rm C} = -2  \rm{mA}$	-600	-650	-750	mV
		$I_{\rm C} = -10 \text{ mA}$	-	-	-820	mV
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	2.3	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = -0.5 V;$ $I_{C} = i_{c} = 0 A; f = 1 MHz$	-	10	-	pF
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	100	-	-	MHz
NF	noise figure		-	1.6	-	dB
		$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -0.2 \text{ mA};$ $R_{S} = 2 \text{ k}\Omega; \text{ f} = 1 \text{ kHz};$ B = 200  Hz	-	2.9	-	dB

#### **NXP Semiconductors**

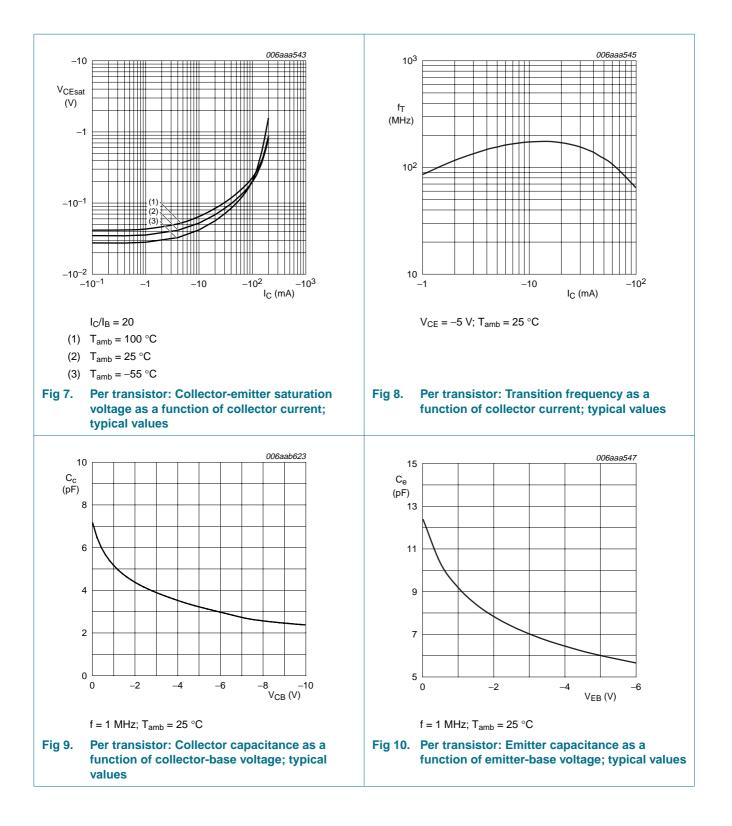
## BC856BS

#### 65 V, 100 mA PNP/PNP general-purpose transistor



BC856BS 1

#### 65 V, 100 mA PNP/PNP general-purpose transistor



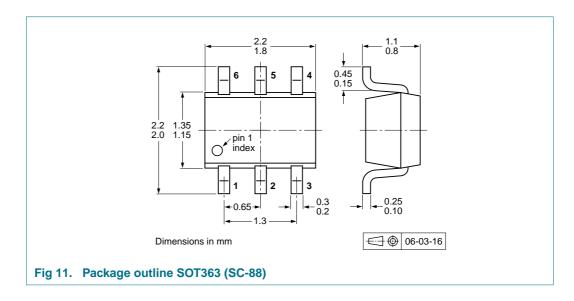
#### 65 V, 100 mA PNP/PNP general-purpose transistor

### 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



## **10. Packing information**

#### Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing	g quantity
				3000	10000
BC856BS	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-165

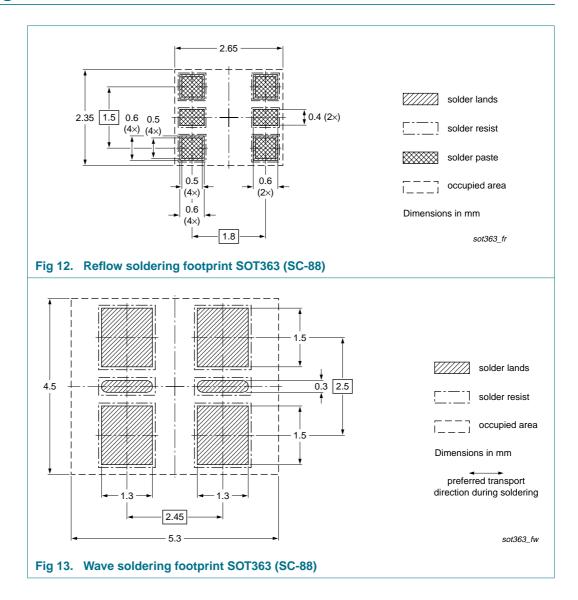
[1] For further information and the availability of packing methods, see <u>Section 14</u>.

[2] T1: normal taping

[3] T2: reverse taping

65 V, 100 mA PNP/PNP general-purpose transistor

## **11. Soldering**



## 65 V, 100 mA PNP/PNP general-purpose transistor

## **12. Revision history**

Table 10. Revision his	Ible 10. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BC856BS_1	20090811	Product data sheet	-	-	

## **13. Legal information**

#### 13.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

#### 13.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

#### 13.3 Disclaimers

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <a href="http://www.nxp.com/profile/terms">http://www.nxp.com/profile/terms</a>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

**Export control** — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

**Quick reference data** — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

#### 13.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

### 14. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

BC856BS\_1 Product data sheet

#### 65 V, 100 mA PNP/PNP general-purpose transistor

## **15. Contents**

1	Product profile 1
1.1	General description
1.2	Features
1.3	Applications 1
1.4	Quick reference data
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 4
7	Characteristics 5
8	Test information 8
8.1	Quality information 8
9	Package outline 8
10	Packing information 8
11	Soldering 9
12	Revision history 10
13	Legal information 11
13.1	Data sheet status 11
13.2	Definitions 11
13.3	Disclaimers
13.4	Trademarks 11
14	Contact information 11
15	Contents 12

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

© NXP B.V. 2009.

All rights reserved.

For more information, please visit: http://www.nxp.com For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 11 August 2009 Document identifier: BC856BS\_1



## **Mouser Electronics**

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

NXP: BC856BS,135 BC856BS,115